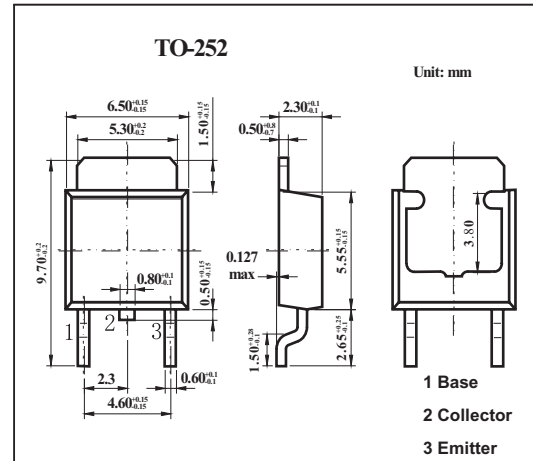


## Silicon PNP Epitaxial

## 2SB1407S

## ■ Features

- Low frequency power amplifier.



## ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector to base voltage	V <sub>CB0</sub>	-35	V
Collector to emitter voltage	V <sub>CEO</sub>	-35	V
Emitter to base voltage	V <sub>EB0</sub>	-5	V
Collector current	I <sub>C</sub>	-2.5	A
Peak collector current	I <sub>CP</sub>	-3	A
Collector power dissipation	P <sub>C</sub>	18	W
Junction temperature	T <sub>J</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

## ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector to base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = -1 mA, I <sub>E</sub> = 0	-35			V
Collector to emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = -10 mA, R <sub>BE</sub> = ∞	-35			V
Emitter to base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = -1 mA, I <sub>C</sub> = 0	-5			V
Collector cutoff current	I <sub>CBO</sub>	V <sub>CB</sub> = -35 V, I <sub>E</sub> = 0			-20	μA
DC current transfer ratio	h <sub>FE</sub>	V <sub>CE</sub> = -2 V, I <sub>C</sub> = -0.5 A	60		320	
		V <sub>CE</sub> = -2 V, I <sub>C</sub> = -1.5 A	20			
Base to emitter voltage	V <sub>BE</sub>	V <sub>CE</sub> = -2 V, I <sub>C</sub> = -1.5 A			-1.5	V
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = -2 A, I <sub>B</sub> = -0.2 A			-1.0	V

## ■ hFE Classification

Rank	B	C	D
hFE	60~120	100~200	160~320